IN THE CLAIMS:

Please amend the claims as follows:

Claim 2. (Amended) A 3-5 group compound semiconductor having a structure in which a layer (B) composed of a 3-5 group compound semiconductor represented by the general formula $In_uGa_vAl_wN$ (u+v+w=1, $0 \leq u \leq 1$, $0 \leq v \leq 1$, $0 \leq w \leq 1$) is adjacent to a layer (A) composed of a 3-5 group compound semiconductor represented by the general formula $In_xGa_yAl_zN$ (x+y+z=1, $0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq z \leq 1$) in which the concentration of an n-type carrier is 1×10^{17} cm^{-3} or less, wherein the concentration of a p-type dopant is 1×10^{17} cm^{-3} or more and 1×10^{21} cm^{-3} or less, and the band gap is larger than that of said layer (B).

Claim 3. (Amended) A 3-5 group compound semiconductor having a [illegible] in which a layer (A) composed of a 3-5 group compound semiconductor represented by the general formula $In_xGa_yAl_zN$ x+y+z=1, [illegible] x [illegible], [illegible] y [illegible], [illegible] z [illegible] in which the concentration of an n-type carrier is [illegible] cm [illegible] or less, wherein the concentration of a p-type dopant is [illegible] cm [illegible] or more and [illegible] cm [illegible] or less, and the band gap is larger than that of said layer (B).

Claim 4. (Amended) A 3-5 group compound semiconductor having a structure comprising at least one layer A composed of a 3-5 group compound semiconductor represented by the general formula $In_xGa_yAl_zN$ ($x+y+z=1$, $0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq z \leq 1$) in which the concentration of an n-type carrier is 1×10^{17} cm^{-3} or less, wherein the concentration of a p-type dopant is 1×10^{17} cm^{-3} or more and 1×10^{21} cm^{-3} or less, between a layer (B) composed of a 3-5 group compound semiconductor represented by the general formula $In_uGa_vAl_wN$ ($u+v+w=1$, $0 < u \leq 1$, $0 \leq v < 1$, $0 \leq w < 1$) and a layer (C) composed of a p-type 3-5 group compound semiconductor represented by the general formula $In_aGa_bAl_cN$ ($a+b+c=1$, $0 \leq a \leq 1$, $0 \leq b \leq 1$, $0 \leq c \leq 1$).

Claim 5. (Amended) A 3-5 group compound semiconductor having a structure comprising a layer B composed of a 3-5 group compound semiconductor represented by the general formula $In_uGa_vAl_wN$ ($u+v+w=1$, $0 < u \leq 1$, $0 \leq v < 1$, $0 \leq w < 1$) carrying thereon a laminated layer C composed of a p-type 3-5 group compound semiconductor represented by the general formula

[illegible]

represented by the general formula $In_xGa_yAl_zN$ (x+y+z=1, $0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq z \leq 1$) in which the concentration of an n-type carrier is 1×10^{17} cm^{-3} or less, wherein the concentration of a p-type dopant is 1×10^{17} cm^{-3} or more and 1×10^{22} cm^{-3} or less, between said layer (D) composed of the n-type 3-5 group compound semiconductor and a layer (C) composed of a p-type 3-5 group compound semiconductor represented by the general formula $In_aGa_bAl_cN$ (a+b+c=1, $0 \leq a \leq 1$, $0 \leq b \leq 1$, $0 \leq c \leq 1$), on the opposite side to said layer (B).

Claim 6. (Amended) The 3-5 group compound semiconductor according to any one of claims 1 to 5 wherein the p-type dopant is Mg and/or Zn.

Claim 7. (Amended) A method of producing a 3-5 group [illegible] semiconductor according to any one of claims 1 to 5, [illegible] represented by the general formula $In_xGa_yAl_zN$ (x+y+z=1, $0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq z \leq 1$) in which the concentration of an n-type [illegible] 1×10^{17} cm^{-3} or less, wherein the concentration of a p-type [illegible]

[illegible]

Claim 8. Amended) A light emitting device obtained by using a 3-5 group compound semiconductor according to any one of claims 1 to 6.

Please add the following new claim:

--Claim 9. The 3-5 group compound semiconductor according to claim 1, wherein a single layer contains the n-type carrier and the p-type dopant.--